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a bulk substrate;
a phase-change material over said substrate;
a buried line of a first conductivity type formed in said substrate, said
buried line including a more lightly doped region over a more heavily doped region and a
more lightly doped region under said more heavily doped region; and
a region of a second conductivity type opposite said first conductivity type
over said line and under said phase-change material.

Please amend claim 21 as follows:

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21 (Amended). An electronic device comprising:
a system memory circuit including:
a bulk substrate;
a phase-change material over said substrate;
a conductive line of a first conductivity type in said substrate, said
line including a more heavily doped region sandwiched between more lightly doped
regions, said conductive line providing signals to said phase-change material; and
a region of a second conductivity type between said phase-change
material and said conductive line; and
a processor coupled to said system memory circuit.

REMARKS

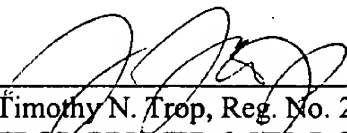
In the previous office action, the Examiner has read the substrate broad enough to include bulk substrates, such as bulk silicon, as well as an epitaxial layer over the bulk silicon substrate. As now amended, this reading is not appropriate. Moreover, the attempt to include doped regions in the epitaxial layer is strained since those regions, as positioned, would have no affect on the buried word line that is in the bulk silicon substrate. However, as amended, the claims are more specifically refined to clearly distinguish over the references that have been cited previously.

In view of these remarks, the application should now be in condition for allowance.

Respectfully requested,

Date:

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